

MBR60200WT

Green products

Technical Data Data Sheet N1553, REV. -

MBR60200WT SCHOTTKY RECTIFIER

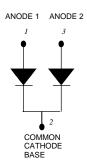
Applications:

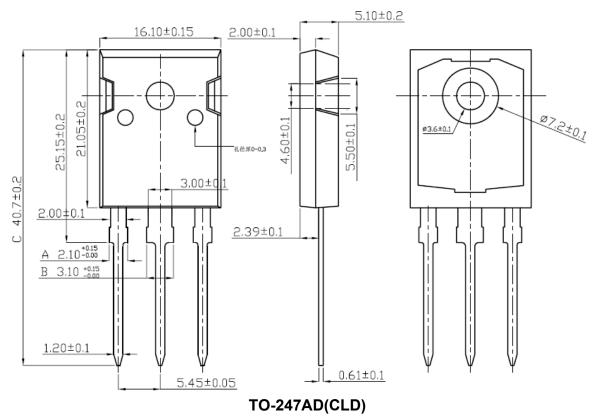
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

Features:

- 175°C T_J operation
- Center tap TO-247AD package
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm





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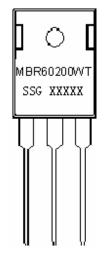


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Marking Diagram:



Where XXXXX is YYWWL

MBR	= Device Type
60	= Forward Current (60A)
200	= Reverse Voltage (200V)
WT	= Configuration
SSG	= SSG
ΥY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBR60200WT	TO-247AD (Pb-Free)	30pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	200	V
Average Forward Current	I _{F(AV)}	50% duty cycle @T _c =110°C, rectangular wave form	60	А
Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	400	А



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Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop (per leg) *	V _{F1}	@ 30A, Pulse, T _J = 25 °C	0.90	V
Reverse Current (per leg) *	I _{R1}	@V _R = rated V _R T _J = 25 °C	0.05	mA
	I _{R2}	$@V_R = rated V_R$ T _J = 100 °C	20	mA
Junction Capacitance (per leg)	Ст	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	600	pF
Typical Series Inductance (per leg)	Ls	Measured lead to lead 5 mm from package body	8.0	nH
Voltage Rate of Change	dv/dt	-	10,000	V/µs

* Pulse Width < 300µs, Duty Cycle <2%

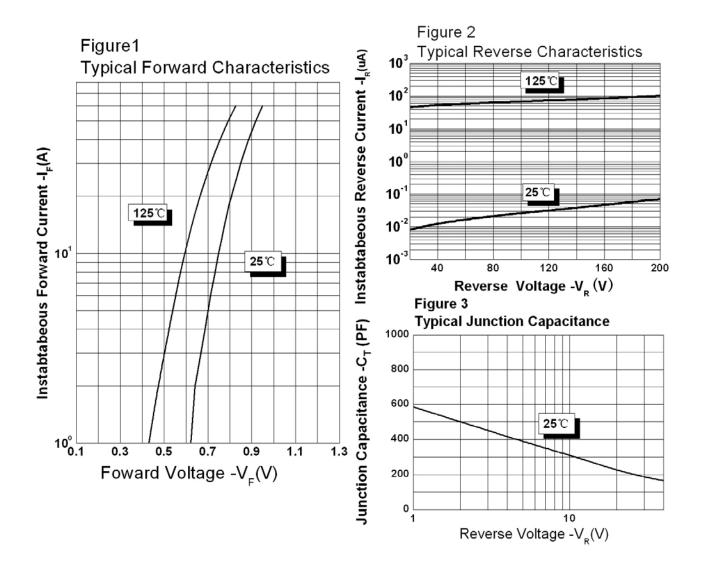
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Maximum Thermal Resistance Junction to Case	R _{θJC}	DC operation	1.5	°C/W
Approximate Weight	wt	-	6.28	g
Case Style		TO-247AD		



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